

Title (en)
METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES HALBLEITERBAUELEMENTS

Title (fr)
PROCÉDÉ DE FABRICATION D' UN DISPOSITIF SEMI-CONDUCTEUR

Publication
EP 2064740 A1 20090603 (EN)

Application
EP 08826921 A 20080807

Priority

- JP 2008064560 W 20080807
- JP 2007206066 A 20070808

Abstract (en)
[origin: WO2009020241A1] A semiconductor device includes a semiconductor construct (2) constructed by a semiconductor substrate (4) and a plurality of external connection electrodes (13) provided under the semiconductor substrate. A lower insulating film (1) is provided under and outside the semiconductor construct. A sealing film (28) is provided on the lower insulating film to cover a periphery of the semiconductor construct. A plurality of lower wiring lines (22) are provided under the lower insulating film and connected to the external connection electrodes of the semiconductor construct, respectively.

IPC 8 full level
H01L 23/31 (2006.01); **H01L 21/56** (2006.01)

CPC (source: EP KR US)
H01L 21/568 (2013.01 - EP US); **H01L 21/6835** (2013.01 - EP US); **H01L 23/31** (2013.01 - KR); **H01L 23/3128** (2013.01 - EP US); **H01L 23/3135** (2013.01 - EP US); **H01L 23/52** (2013.01 - KR); **H01L 23/5389** (2013.01 - EP US); **H01L 24/19** (2013.01 - EP US); **H01L 24/96** (2013.01 - EP US); **H01L 24/97** (2013.01 - EP US); **H01L 25/16** (2013.01 - EP US); **H01L 23/3114** (2013.01 - EP US); **H01L 2221/68345** (2013.01 - EP US); **H01L 2224/04105** (2013.01 - EP US); **H01L 2224/12105** (2013.01 - EP US); **H01L 2224/20** (2013.01 - EP US); **H01L 2224/211** (2013.01 - EP US); **H01L 2224/24195** (2013.01 - EP US); **H01L 2224/32225** (2013.01 - EP US); **H01L 2224/92144** (2013.01 - EP US); **H01L 2224/97** (2013.01 - EP US); **H01L 2924/01006** (2013.01 - EP US); **H01L 2924/01013** (2013.01 - EP US); **H01L 2924/01015** (2013.01 - EP US); **H01L 2924/01029** (2013.01 - EP US); **H01L 2924/01033** (2013.01 - EP US); **H01L 2924/01047** (2013.01 - EP US); **H01L 2924/01058** (2013.01 - EP US); **H01L 2924/01078** (2013.01 - EP US); **H01L 2924/01087** (2013.01 - EP US); **H01L 2924/07802** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/15174** (2013.01 - EP US); **H01L 2924/15311** (2013.01 - EP US); **H01L 2924/181** (2013.01 - EP US); **H01L 2924/19041** (2013.01 - EP US); **H01L 2924/19043** (2013.01 - EP US); **H01L 2924/19105** (2013.01 - EP US)

C-Set (source: EP US)

1. **H01L 2224/97 + H01L 2224/82**
2. **H01L 2224/97 + H01L 2924/15311**
3. **H01L 2924/07802 + H01L 2924/00**
4. **H01L 2924/181 + H01L 2924/00012**

Citation (search report)
See references of WO 2009020241A1

Designated contracting state (EPC)
DE FR GB

Designated extension state (EPC)
AL BA MK RS

DOCDB simple family (publication)
WO 2009020241 A1 20090212; CN 101548378 A 20090930; CN 101548378 B 20120502; EP 2064740 A1 20090603; JP 2009043857 A 20090226; KR 101084924 B1 20111117; KR 20090085573 A 20090807; TW 200913216 A 20090316; TW I427755 B 20140221; US 2009039510 A1 20090212

DOCDB simple family (application)
JP 2008064560 W 20080807; CN 200880000828 A 20080807; EP 08826921 A 20080807; JP 2007206066 A 20070808; KR 20097006272 A 20080807; TW 97129987 A 20080807; US 18776608 A 20080807